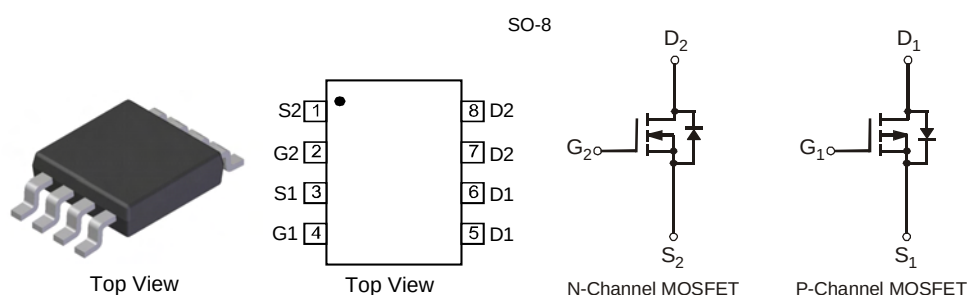


Features

- Low On-Resistance
- N-Channel: 21mΩ @ 10V
32mΩ @ 4.5V
- P-Channel: 39mΩ @ 10V
53mΩ @ 4.5V
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Complementary Pair MOSFET
- **Lead Free/RoHS Compliant (Note 1)**
- **"Green" Device (Note 2)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Mechanical Data

- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound.
UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram
- Terminals: Finish - Matte Tin annealed over Copper lead frame.
Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 6
- Ordering Information: See Page 6
- Weight: 0.072 grams (approximate)



Maximum Ratings N-CHANNEL – Q1 @T_A = 25°C unless otherwise specified

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	30	V
Gate-Source Voltage			V _{GSS}	±20	V
Continuous Drain Current (Note 3)	Steady State	T _A = 25°C	I _D	8.5	A
		T _A = 85°C		7.1	
Pulsed Drain Current (Note 4)			I _{DM}	26	A

Maximum Ratings P-CHANNEL – Q2 @T_A = 25°C unless otherwise specified

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	-30	V
Gate-Source Voltage			V _{GSS}	±20	V
Continuous Drain Current (Note 3)	Steady State	T _A = 25°C	I _D	-7.0	A
		T _A = 85°C		-4.5	
Pulsed Drain Current (Note 4)			I _{DM}	-25	A

Thermal Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 3)	P _D	2.5	W
Thermal Resistance, Junction to Ambient (Note 3)	R _{θJA}	50	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

- Notes:
1. No purposefully added lead.
 2. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
 3. Device mounted on FR-4 PCB, with minimum recommended pad layout.
 4. Repetitive rating, pulse width limited by junction temperature.

Electrical Characteristics N-CHANNEL – Q1 @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 5)						
Drain-Source Breakdown Voltage	BV_{DSS}	30	-	-	V	$V_{GS} = 0V, I_D = 250\mu A$
Zero Gate Voltage Drain Current $T_J = 25^\circ\text{C}$	I_{DSS}	-	-	1.0	μA	$V_{DS} = 30V, V_{GS} = 0V$
Gate-Source Leakage	I_{GSS}	-	-	± 100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 5)						
Gate Threshold Voltage	$V_{GS(th)}$	1	1.45	2.1	V	$V_{DS} = V_{GS}, I_C = 250\mu A$
Static Drain-Source On-Resistance	$R_{DS(on)}$	-	14	21	m Ω	$V_{GS} = 10V, I_C = 7A$
			18	32		$V_{GS} = 4.5V, I_C = 5.6A$
Forward Transfer Admittance	$ Y_{fs} $	-	8.1	-	S	$V_{DS} = 5V, I_C = 7A$
Diode Forward Voltage (Note 5)	V_{SD}	-	0.7	1.0	V	$V_{GS} = 0V, I_S = 1A$
DYNAMIC CHARACTERISTICS (Note 6)						
Input Capacitance	C_{iss}	-	767	-	pF	$V_{DS} = 10V, V_{GS} = 0V, f = 1.0MHz$
Output Capacitance	C_{oss}	-	110	-	pF	
Reverse Transfer Capacitance	C_{rss}	-	105	-	pF	
Gate Resistance	R_g	-	1.4	-	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$
Total Gate Charge (4.5V)	Q_g	-	7.8	-	nC	$V_{GS} = 10V, V_{DS} = 15V, I_D = 9A$
Total Gate Charge (10V)	Q_g	-	16.1	-	nC	
Gate-Source Charge	Q_{gs}	-	1.8	-	nC	
Gate-Drain Charge	Q_{gd}	-	2.5	-	nC	
Turn-On Delay Time	$t_{D(on)}$	-	5.0	-	ns	$V_{GS} = 10V, V_{DS} = 15V, R_G = 6\Omega, I_D = 1A$
Turn-On Rise Time	t_r	-	4.5	-	ns	
Turn-Off Delay Time	$t_{D(off)}$	-	26.3	-	ns	
Turn-Off Fall Time	t_f	-	8.55	-	ns	

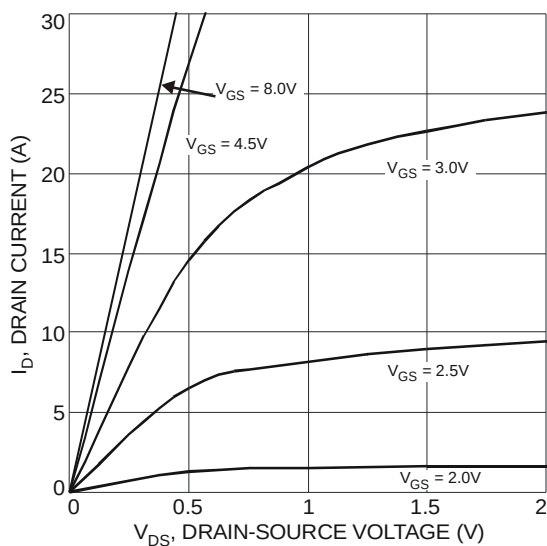


Fig. 1 Typical Output Characteristics

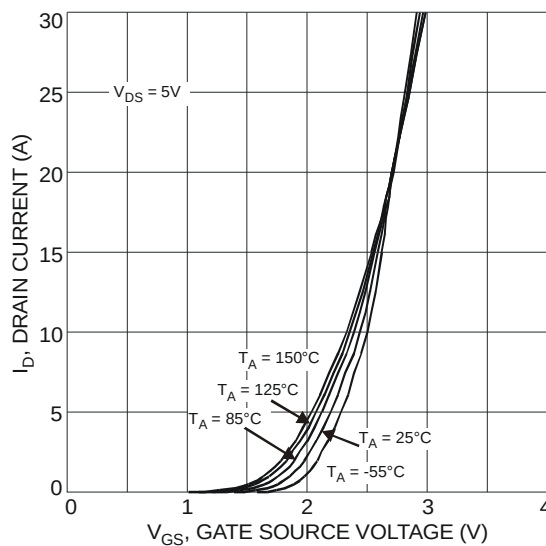


Fig. 2 Typical Transfer Characteristics

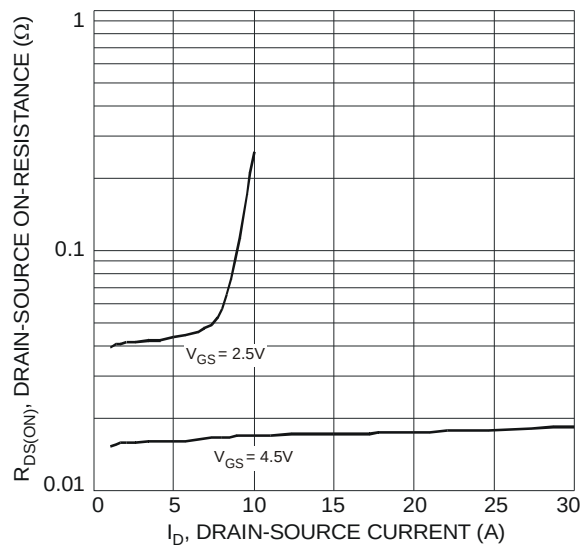


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

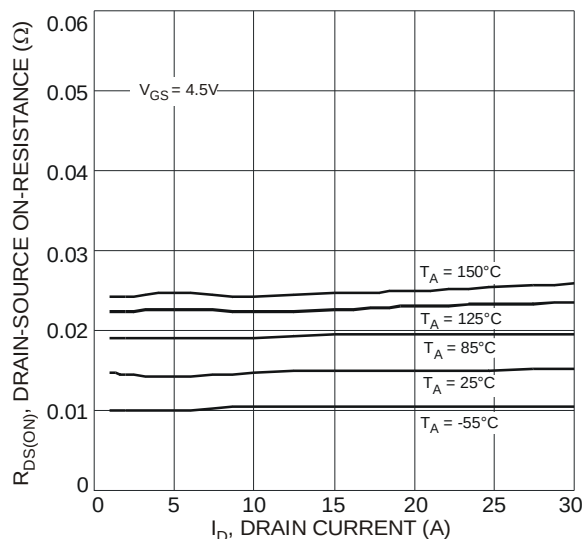


Fig. 4 Typical Drain-Source On-Resistance vs. Drain Current and Temperature

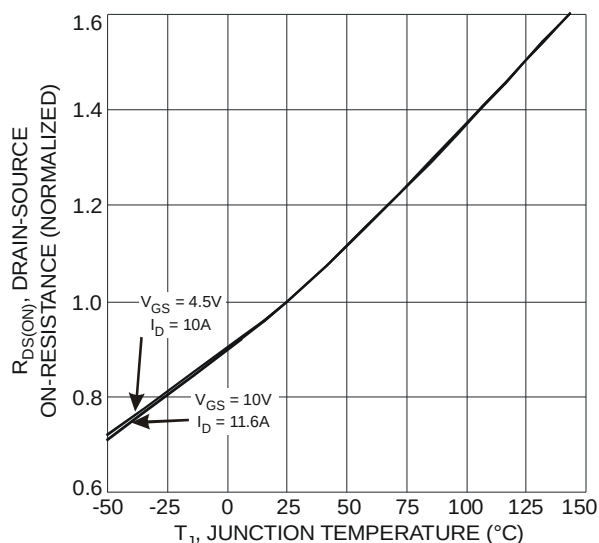


Fig. 5 On-Resistance Variation with Temperature

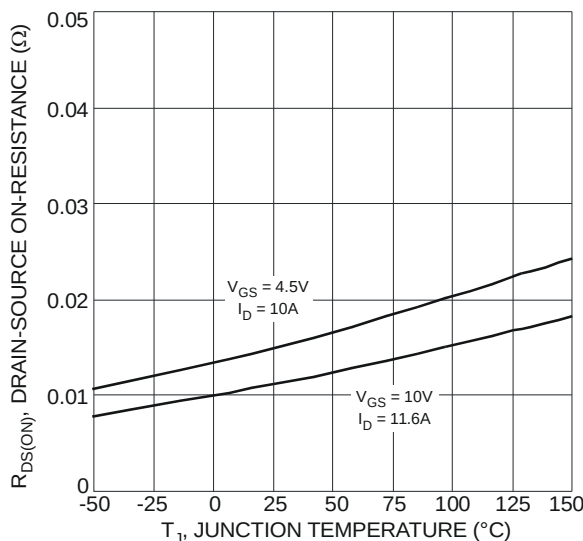


Fig. 6 On-Resistance Variation with Temperature

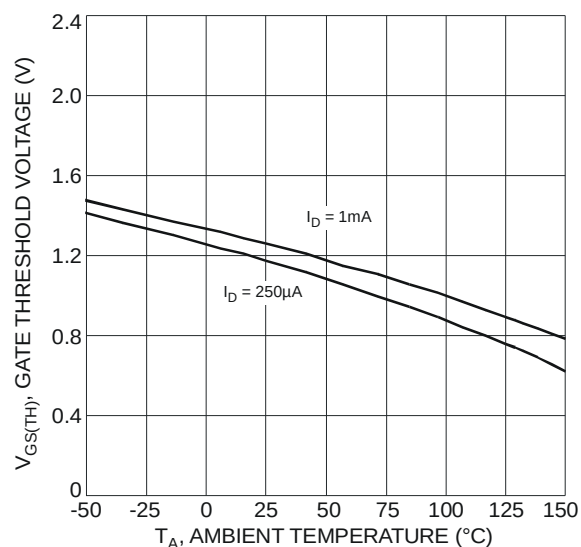


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

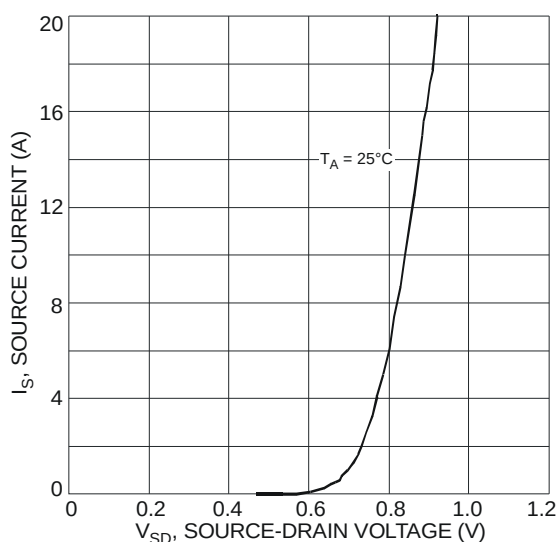
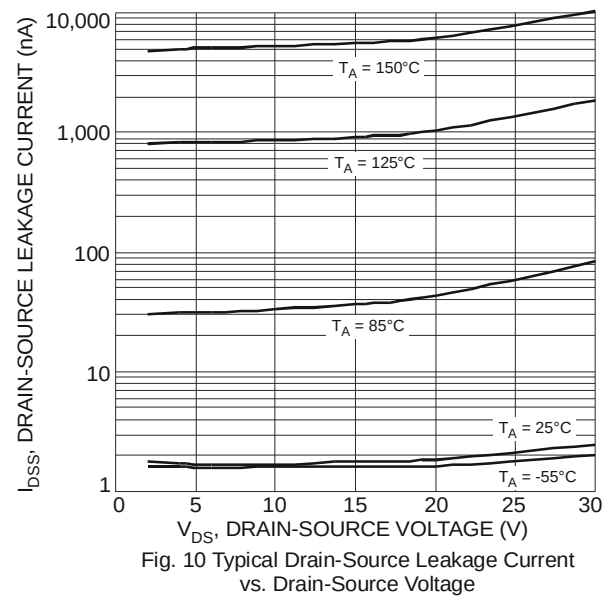
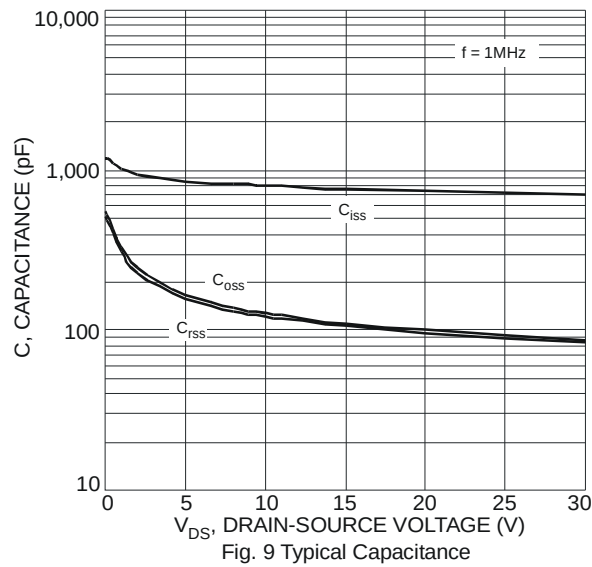


Fig. 8 Diode Forward Voltage vs. Current



Electrical Characteristics P-CHANNEL @TA = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 5)						
Drain-Source Breakdown Voltage	BV _{DSS}	-30	-	-	V	V _{GS} = 0V, I _D = -250μA
Zero Gate Voltage Drain Current T _J = 25°C	I _{DSS}	-	-	-1.0	μA	V _{DS} = -30V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	-	-	±100	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 5)						
Gate Threshold Voltage	V _{GS(th)}	-1	-1.7	-2.2	V	V _{DS} = V _{GS} , I _D = -250μA
Static Drain-Source On-Resistance	R _{DS(on)}	-	30	39	mΩ	V _{GS} = -10V, I _D = -4.3A
			42	53		V _{GS} = -4.5V, I _D = -3.7A
Forward Transfer Admittance	Y _{fs}	-	7	-	S	V _{DS} = -5V, I _D = -4.3A
Diode Forward Voltage (Note 5)	V _{SD}	-	-0.75	-1.0	V	V _{GS} = 0V, I _S = -1.7A
DYNAMIC CHARACTERISTICS (Note 6)						
Input Capacitance	C _{iss}	-	1002	-	pF	V _{DS} = -10V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{oss}	-	125	-	pF	
Reverse Transfer Capacitance	C _{rss}	-	118	-	pF	
Gate Resistance	R _g	-	13	-	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge (4.5V)	Q _g	-	10.1	-	nC	V _{GS} = -4.5V, V _{DS} = -15V, I _D = -6A
Total Gate Charge (10V)	Q _g	-	21.1	-	nC	
Gate-Source Charge	Q _{gs}	-	2.8	-	nC	
Gate-Drain Charge	Q _{gd}	-	3.2	-	nC	
Turn-On Delay Time	t _{D(on)}	-	10.1	-	ns	V _{GS} = -10V, V _{DS} = -15V, R _G = 6Ω, I _D = -1A
Turn-On Rise Time	t _r	-	6.5	-	ns	
Turn-Off Delay Time	t _{D(off)}	-	50.1	-	ns	
Turn-Off Fall Time	t _f	-	22.2	-	ns	

Notes: 5. Short duration pulse test used to minimize self-heating effect.
6. Guaranteed by design. Not subject to production testing.

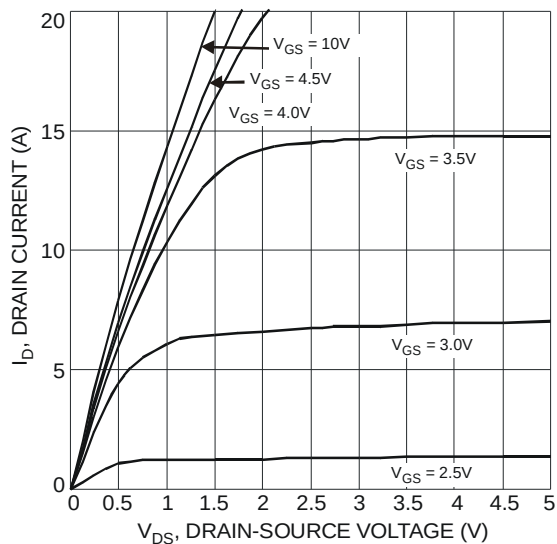


Fig. 11 Typical Output Characteristics

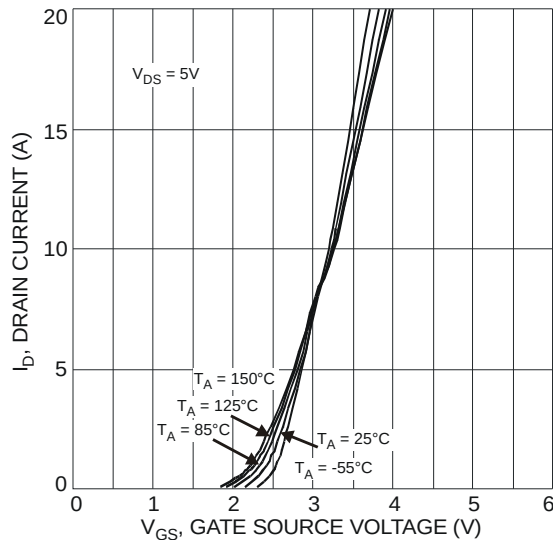


Fig. 12 Typical Transfer Characteristics

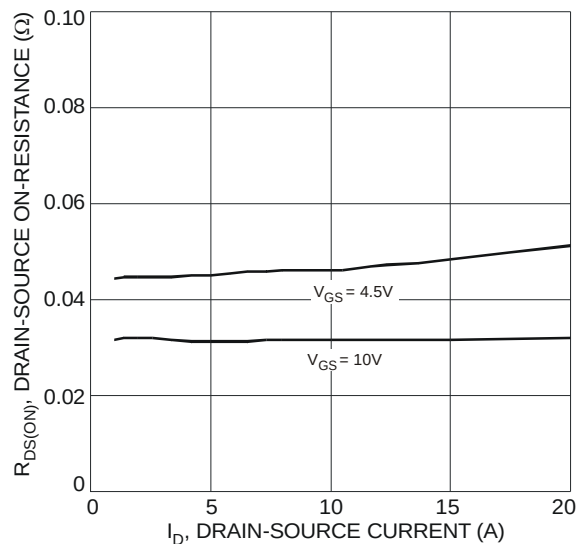


Fig. 13 Typical On-Resistance vs. Drain Current and Gate Voltage

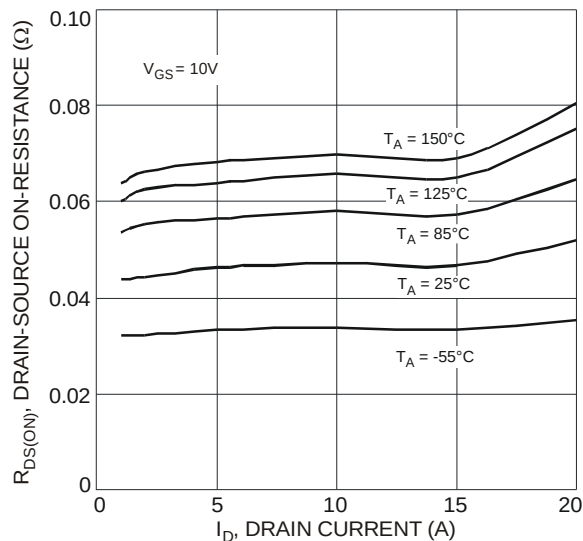


Fig. 14 Typical Drain-Source On-Resistance vs. Drain Current and Temperature

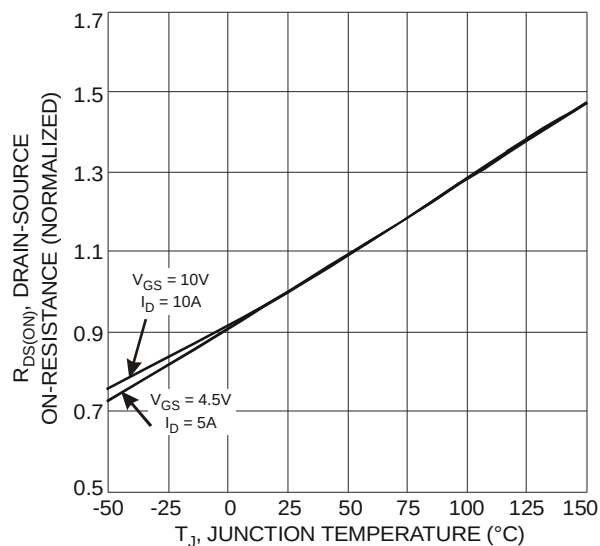


Fig. 15 On-Resistance Variation with Temperature

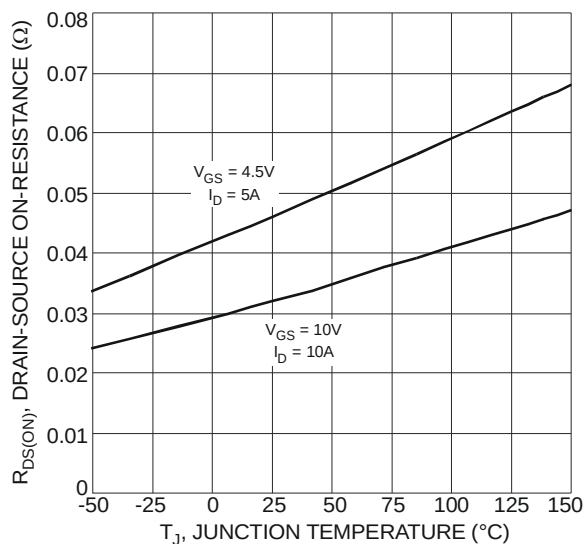


Fig. 16 On-Resistance Variation with Temperature

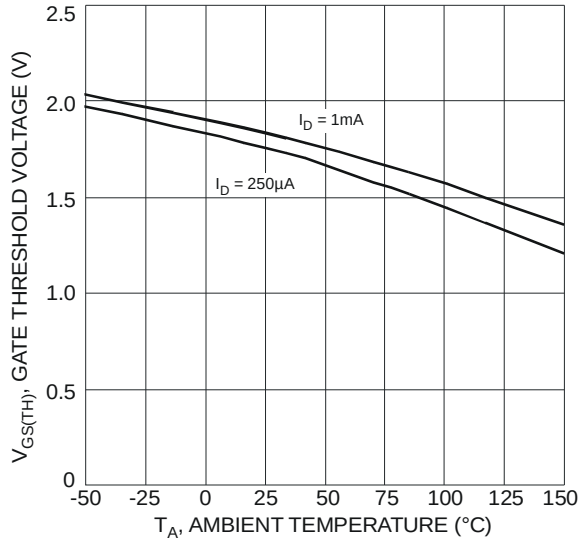


Fig. 17 Gate Threshold Variation vs. Ambient Temperature

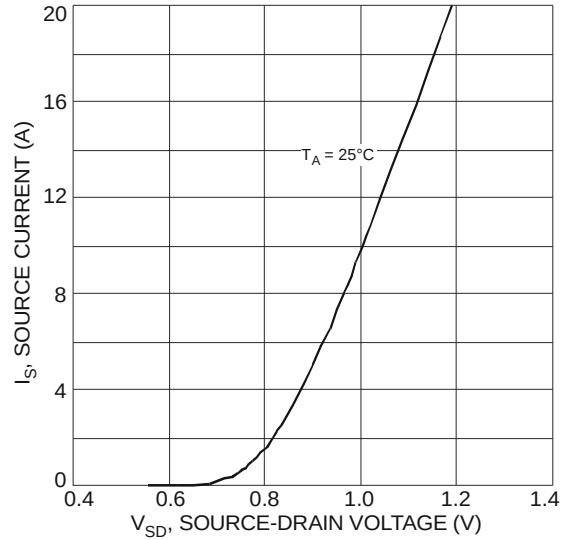


Fig. 18 Diode Forward Voltage vs. Current

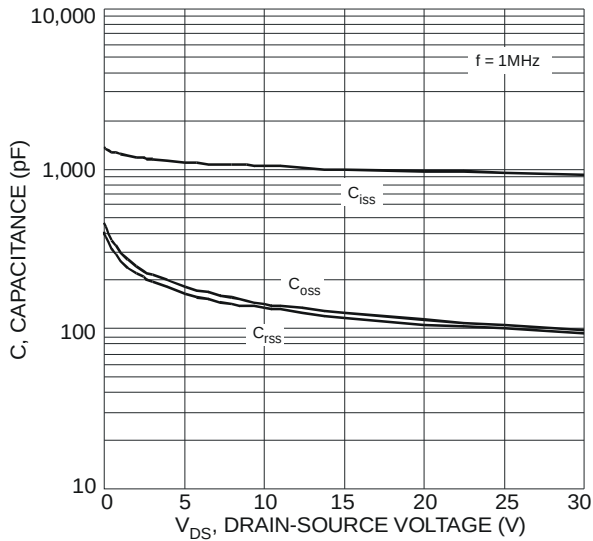


Fig. 19 Typical Capacitance

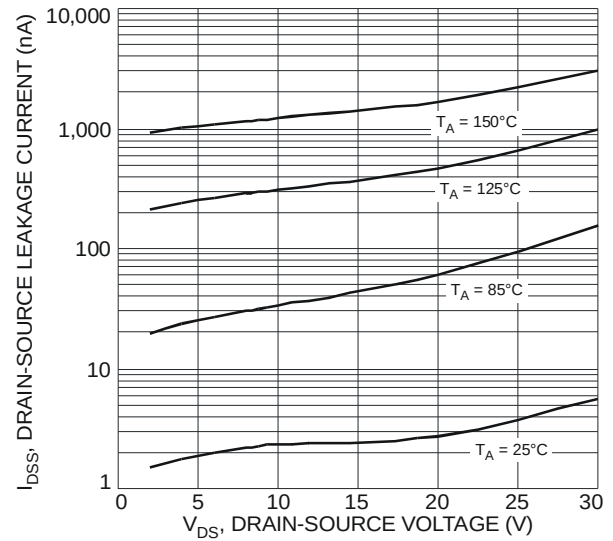


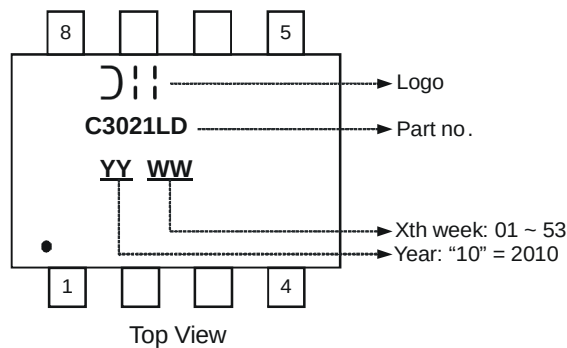
Fig. 20 Typical Drain-Source Leakage Current vs. Drain-Source Voltage

Ordering Information (Note 7)

Part Number	Case	Packaging
DMC3021LSD-13	SO-8	2500/Tape & Reel

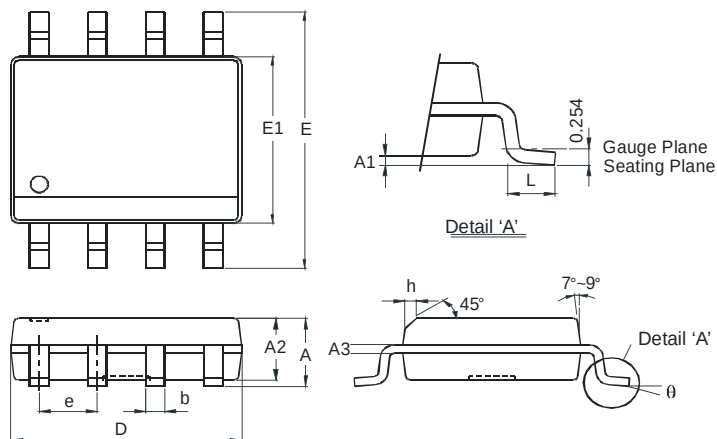
Notes: 7. For packaging details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.

Marking Information



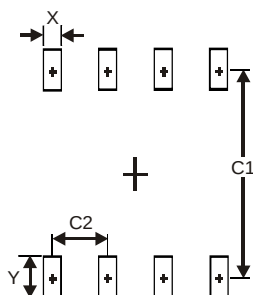
Top View

Package Outline Dimensions



SO-8		
Dim	Min	Max
A	-	1.75
A1	0.10	0.20
A2	1.30	1.50
A3	0.15	0.25
b	0.3	0.5
D	4.85	4.95
E	5.90	6.10
E1	3.85	3.95
e	1.27 Typ	
h	-	0.35
L	0.62	0.82
θ	0°	8°
All Dimensions in mm		

Suggested Pad Layout



Dimensions	Value (in mm)
X	0.60
Y	1.55
C1	5.4
C2	1.27

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